

Title (en)  
PROCESS AND APPARATUS FOR PREPARING BODIES OF SEMICONDUCTOR MATERIAL

Publication  
**EP 0045192 B1 19850918 (EN)**

Application  
**EP 81303401 A 19810724**

Priority  
US 17250380 A 19800728

Abstract (en)  
[origin: EP0045192A2] In a process for preparing a body of semiconductor material in which a slim rod of semiconductor material in a chemical vapor deposition chamber is maintained at a temperature sufficient to decompose gaseous compounds containing semiconductor material, and a reaction gas comprising the said compounds is introduced into the chemical vapor deposition chamber whereby decomposition of the gaseous compounds occurs and semiconductor material is deposited on the slim rod to form an enlarged semiconductor body, a gas curtain is created along the inner wall of the chemical vapor deposition chamber substantially preventing the gaseous compounds from decomposing on the wall. Apparatus for operating the process comprises a chemical vapor deposition chamber (23) having reaction gas entry (32) and exit (35) means, and for the creation of the gas curtain, gas entry means (34) and flow guide means (36).

IPC 1-7  
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IPC 8 full level  
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CPC (source: EP KR US)  
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